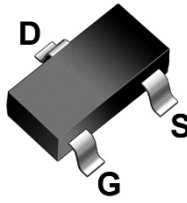
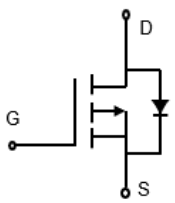



Lonten P-channel -30V, -4.3A, 46mΩ Power MOSFET

<p>Description These P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and with stand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.</p> <p>Features</p> <ul style="list-style-type: none"> ◆ -30V,-4.3A,$R_{DS(ON).max}=46m\Omega@V_{GS}=-10V$ ◆ Improved dv/dt capability ◆ Fast switching ◆ Green device available <p>Applications</p> <ul style="list-style-type: none"> ◆ PWM applications ◆ Load switch ◆ Portable Equipment 	<p>Product Summary</p> <table style="width: 100%; border: none;"> <tr> <td style="padding: 2px;">V_{DSS}</td> <td style="padding: 2px;">-30V</td> </tr> <tr> <td style="padding: 2px;">$R_{DS(on).max}@ V_{GS}=-10V$</td> <td style="padding: 2px;">46mΩ</td> </tr> <tr> <td style="padding: 2px;">I_D</td> <td style="padding: 2px;">-4.3A</td> </tr> </table> <p>Pin Configuration</p> <div style="text-align: center;">  <p>SOT-23-3</p> </div> <div style="text-align: center;">  </div> <p style="text-align: center;">P-Channel MOSFET</p> <div style="text-align: right;">  </div>	V_{DSS}	-30V	$R_{DS(on).max}@ V_{GS}=-10V$	46mΩ	I_D	-4.3A
V_{DSS}	-30V						
$R_{DS(on).max}@ V_{GS}=-10V$	46mΩ						
I_D	-4.3A						

Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-30	V
Continuous drain current ($T_A = 25^\circ\text{C}$)	I_D	-4.3	A
Continuous drain current ($T_A = 100^\circ\text{C}$)		-2.7	A
Pulsed drain current ¹⁾	I_{DM}	-17.2	A
Gate-Source voltage	V_{GSS}	± 20	V
Power Dissipation ($T_A = 25^\circ\text{C}$)	P_D	1.3	W
Storage Temperature Range	T_{STG}	-55 to +150	$^\circ\text{C}$
Operating Junction Temperature Range	T_J	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JA}$	96	$^\circ\text{C/W}$

Package Marking and Ordering Information

Device	Device Package	Marking
LPSA3487	SOT-23-3	3487

Electrical Characteristics
 $T_J = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV_{DSS}	$V_{GS}=0\text{ V}, I_D=-250\mu\text{A}$	-30	---	---	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu\text{A}$	-1.2	-1.7	-2.2	V
Drain-source leakage current	I_{DSS}	$V_{DS}=-30\text{ V}, V_{GS}=0\text{ V}, T_J = 25^\circ\text{C}$	---	---	-1	μA
		$V_{DS}=-24\text{ V}, V_{GS}=0\text{ V}, T_J = 125^\circ\text{C}$	---	---	-10	μA
Gate leakage current, Forward	I_{GSSF}	$V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$	---	---	100	nA
Gate leakage current, Reverse	I_{GSSR}	$V_{GS}=-20\text{ V}, V_{DS}=0\text{ V}$	---	---	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=-10\text{ V}, I_D=-4.3\text{ A}$	---	33	46	m Ω
		$V_{GS}=-4.5\text{ V}, I_D=-3\text{ A}$	---	43	72	m Ω
Forward transconductance	g_{fs}	$V_{DS} = -5\text{ V}, I_D = -4.3\text{ A}$	---	10	---	S
Dynamic characteristics						
Input capacitance	C_{iss}	$V_{DS} = -15\text{ V}, V_{GS} = 0\text{ V},$ $F = 1\text{ MHz}$	---	940	---	pF
Output capacitance	C_{oss}		---	103	---	
Reverse transfer capacitance	C_{rss}		---	88	---	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=-10\text{ V}, V_{GS}=-4.5\text{ V},$ $I_D = -4.3\text{ A}, R_g=3\Omega$	---	4.0	---	ns
Rise time	t_r		---	31.1	---	
Turn-off delay time	$t_{d(off)}$		---	38.9	---	
Fall time	t_f		---	8.9	---	
Gate resistance	R_g	$V_{GS}=0\text{ V}, V_{DS}=0\text{ V}, f=1\text{ MHz}$	---	11	---	Ω
Gate charge characteristics						
Gate to source charge	Q_{gs}	$V_{DS}=-15\text{ V}, I_D=-4.3\text{ A},$ $V_{GS}=-10\text{ V}$	---	2.4	---	nC
Gate to drain charge	Q_{gd}		---	2.9	---	
Gate charge total	Q_g		---	14.8	---	
Drain-Source diode characteristics and Maximum Ratings						
Continuous Source Current	I_S		---	---	-4.3	A
Pulsed Source Current ²⁾	I_{SM}		---	---	-17.2	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0\text{ V}, I_S=-1\text{ A}, T_J=25^\circ\text{C}$	---	---	-1.2	V

Notes:

1: Repetitive Rating: Pulse width limited by maximum junction temperature.

2: Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2\%$.

Electrical Characteristics Diagrams

Figure 1. Typ. Output Characteristics

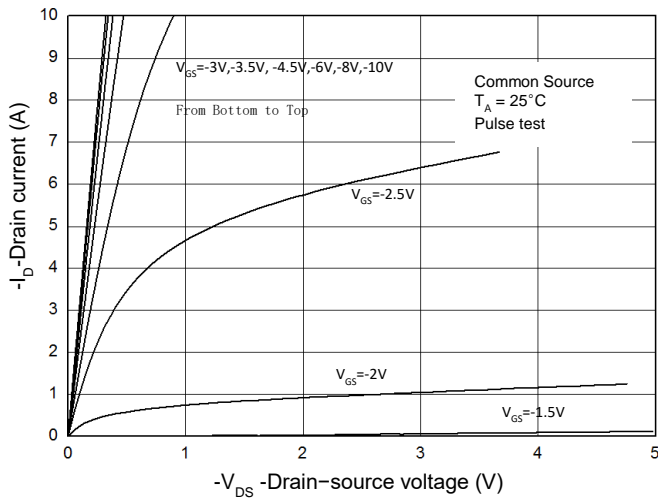


Figure 2. Transfer Characteristics

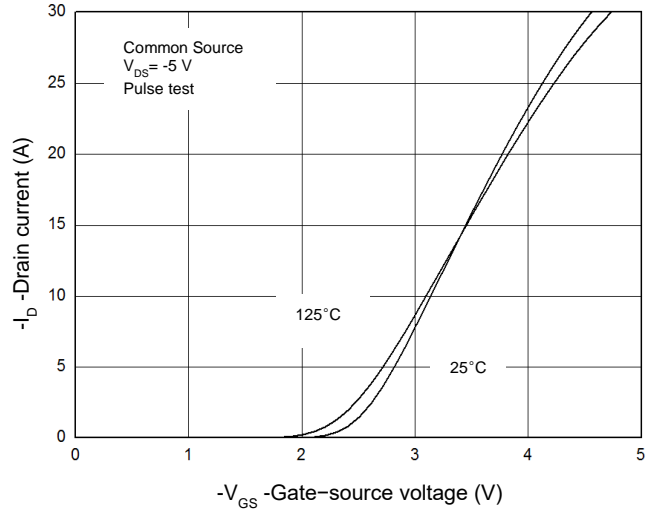


Figure 3. Capacitance Characteristics

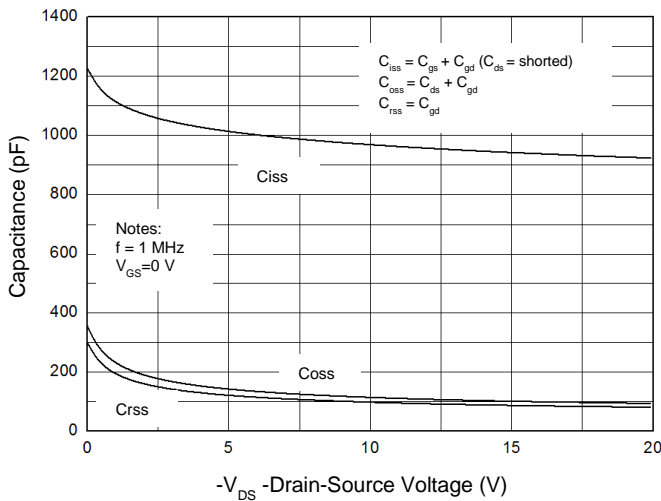


Figure 4. Gate Charge Waveform

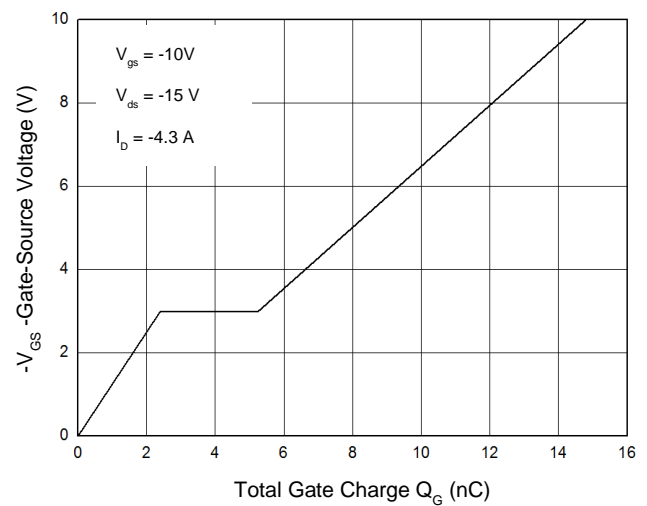


Figure 5. Body-Diode Characteristics

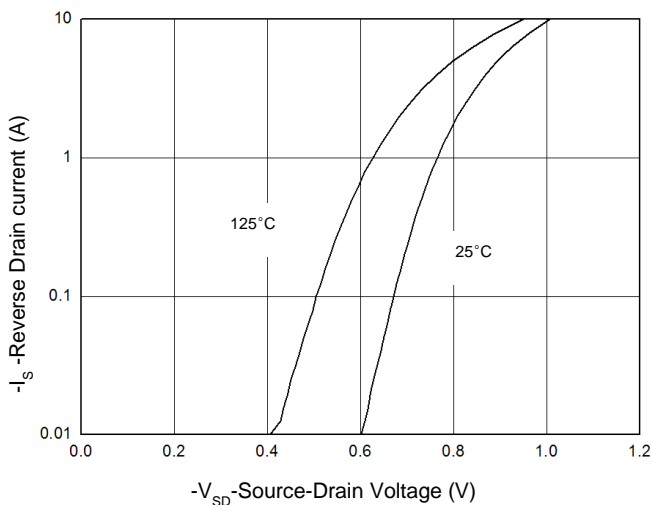


Figure 6. Rdson-Drain Current

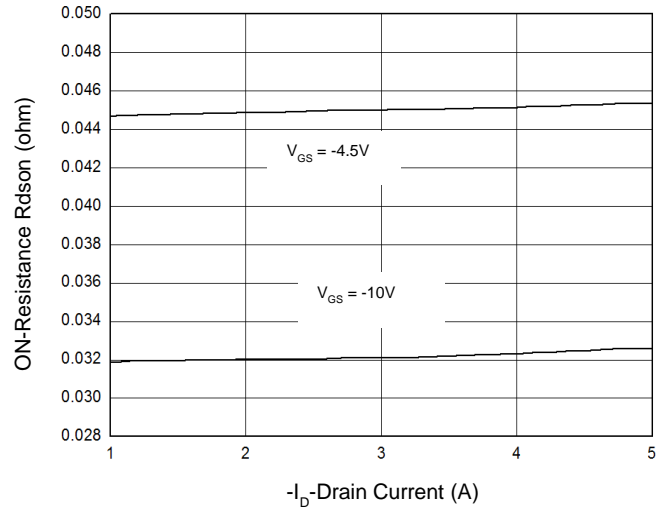


Figure 7. Rds(on)-Junction Temperature(°C)

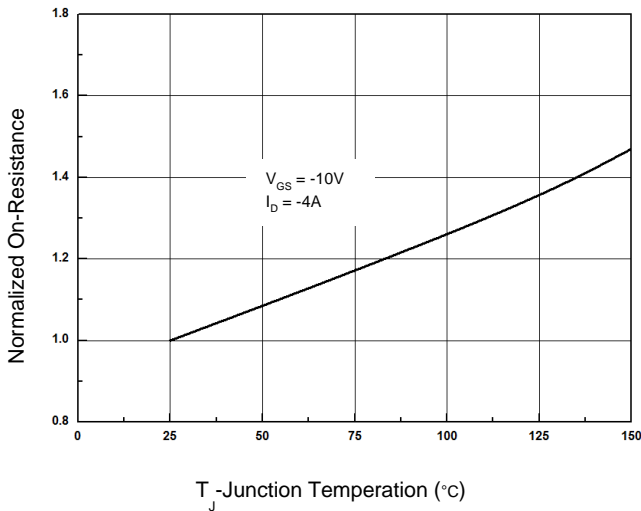


Figure 9. BVdss vs. Junction temperature(°C)

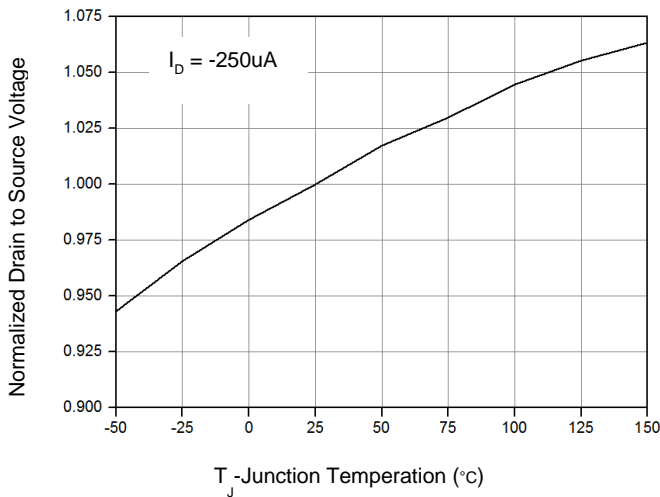


Figure 8. Rds(on) vs Gate Voltage

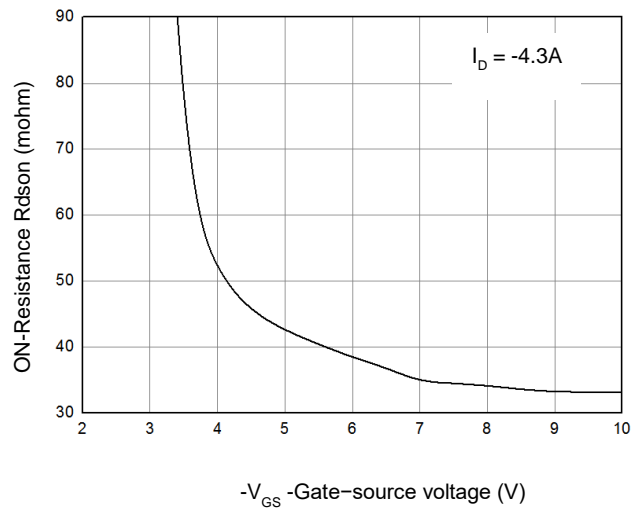


Figure 10. Maximum Safe Operating Area

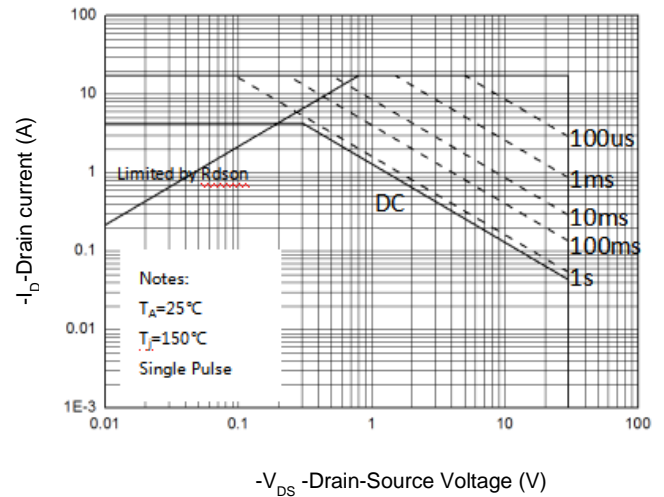
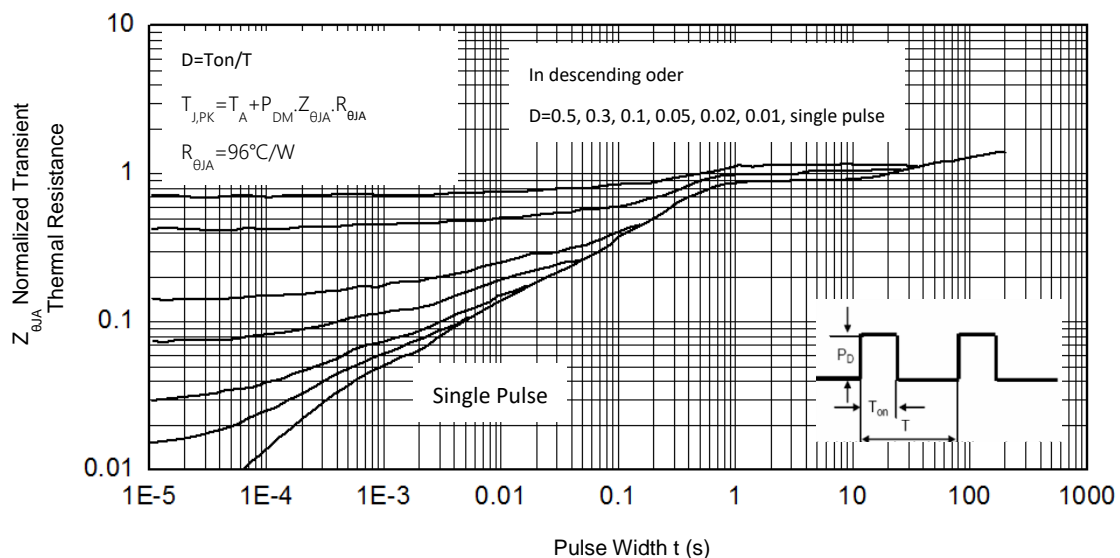


Figure 11. Normalized Maximum Transient Thermal Impedance (RthJA)



Test Circuit & Waveform

Figure 8. Gate Charge Test Circuit & Waveform

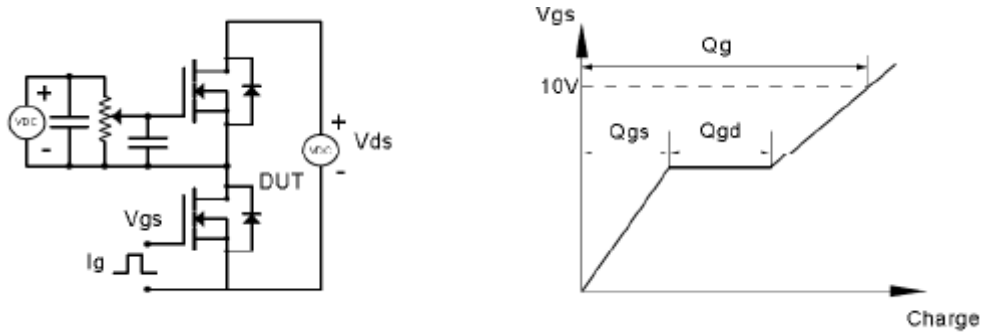


Figure 9. Resistive Switching Test Circuit & Waveforms

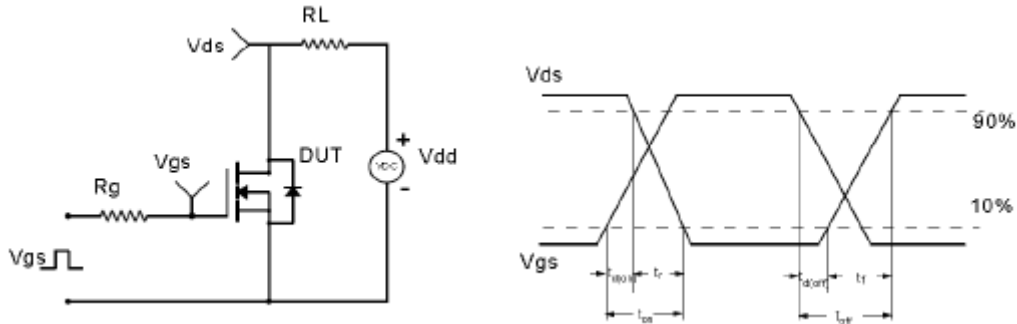


Figure 10. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

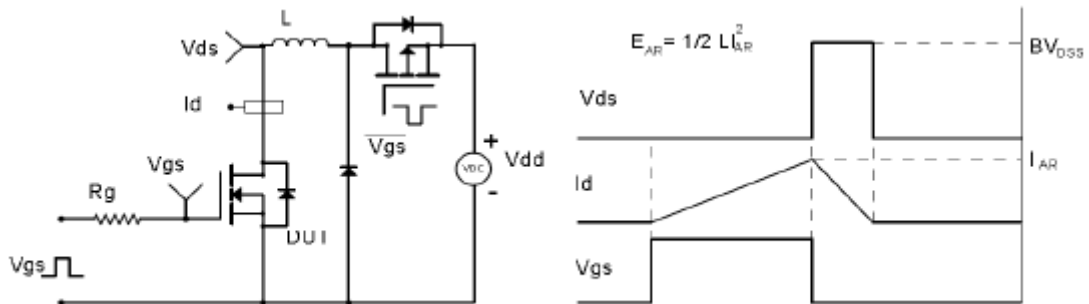
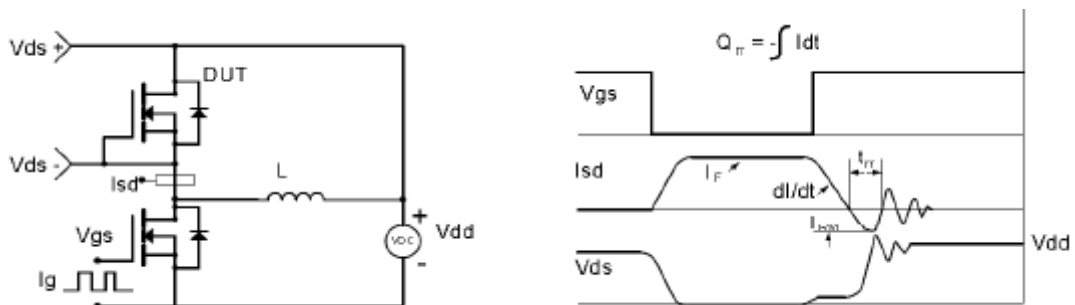
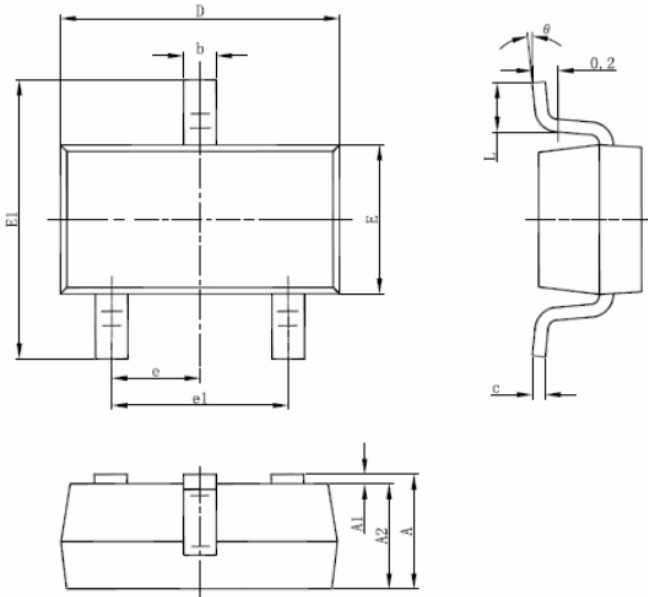


Figure 11. Diode Recovery Circuit & Waveform

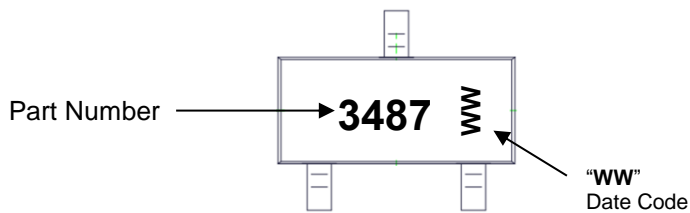


Mechanical Dimensions for SOT-23-3



SYMBOL	COMMON DIMENSIONS			
	MILLIMETERS		INCHS	
	MIN	MAX	MIN	MAX
A	1.00	1.30	0.039	0.051
A1	0.00	0.10	0.000	0.004
A2	1.00	1.20	0.039	0.047
b	0.30	0.50	0.012	0.020
c	0.04	0.21	0.002	0.008
D	2.80	3.00	0.110	0.118
E	1.50	1.70	0.059	0.067
E1	2.60	3.00	0.102	0.118
e	0.95 TYP.		0.037 TYP.	
e1	1.90 TYP.		0.075 TYP.	
L	0.25	0.55	0.010	0.022
θ	0°	8°	0°	8°

SOT-23-3 Part Marking Information



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